



A schematic diagram of a photodiode cross-section. It shows a p-n junction with a p-layer on top and an n-layer at the bottom. A light beam labeled "Incident optical radiation" enters from the left. The depletion region is indicated by dashed lines. Labels include "Buried layer", "G110", "G12", "G13", and "G14". A note states "Absorption coefficient α depends on wavelength".

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